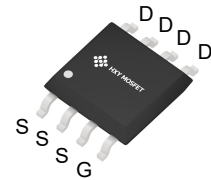




Description

The DMT69M8LSS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

General Features

$V_{DS} = 60V$ $I_D = 10A$

$R_{DS(ON)} < 13m\Omega$ @ $V_{GS}=10V$

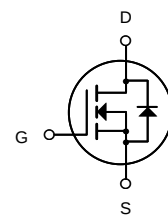
$R_{DS(ON)} < 15m\Omega$ @ $V_{GS}=4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMT69M8LSS	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings ($T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	10	A
$I_D(100^{\circ}C)$	Drain Current-Continuous($T_c=100^{\circ}C$)	8.5	A
I_{DM}	Pulsed Drain Current	30	A
P_D	Maximum Power Dissipation	3	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$



Electrical Characteristics (TC=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.9	1.3	1.8	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	10	13	mΩ
		V _{GS} =4.5V, I _D =5A	-	11.5	15	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =12A	40	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	4100	-	PF
Output Capacitance	C _{OSS}		-	298	-	PF
Reverse Transfer Capacitance	C _{rss}		-	229	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, R _L =1Ω V _{GS} =10V,R _{GEN} =3Ω	-	8.5	-	nS
Turn-on Rise Time	t _r		-	7	-	nS
Turn-Off Delay Time	t _{d(off)}		-	40	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Q _g	V _{DS} =30V,I _D =10A, V _{GS} =10V	-	93	-	nC
Gate-Source Charge	Q _{gs}		-	9.7	-	nC
Gate-Drain Charge	Q _{gd}		-	20	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =10A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	10	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =10A di/dt = 100A/μs ^(Note3)	-	32	-	nS
Reverse Recovery Charge	Q _{rr}		-	45	-	nC

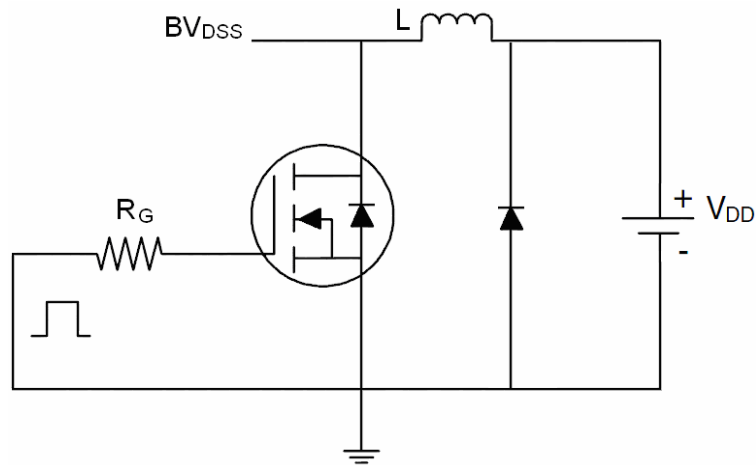
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$. The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

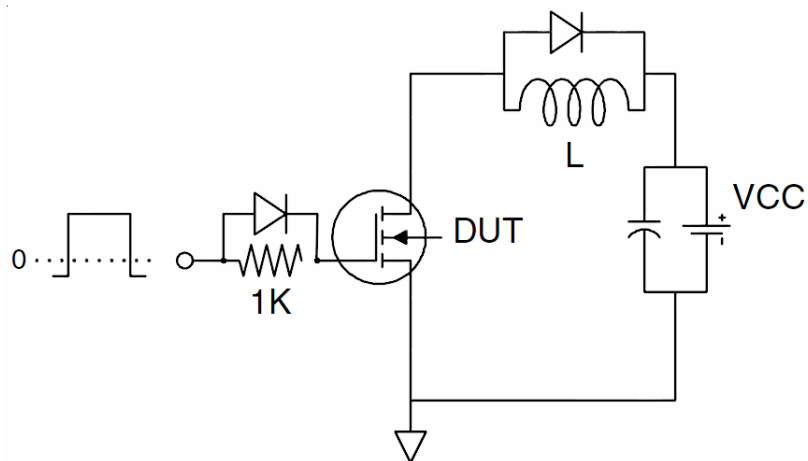


Test Circuit

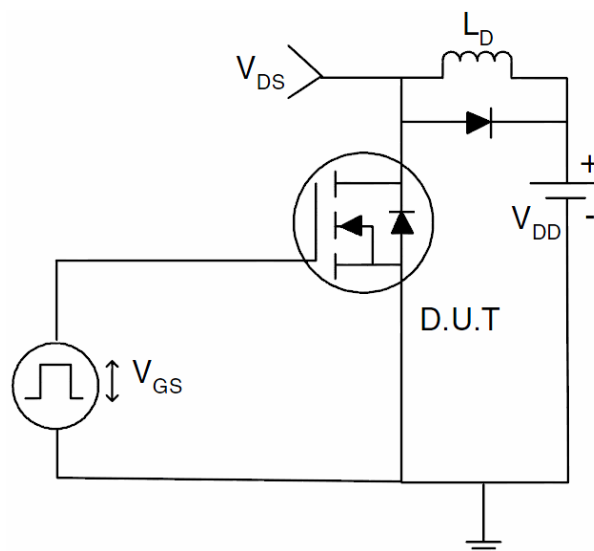
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

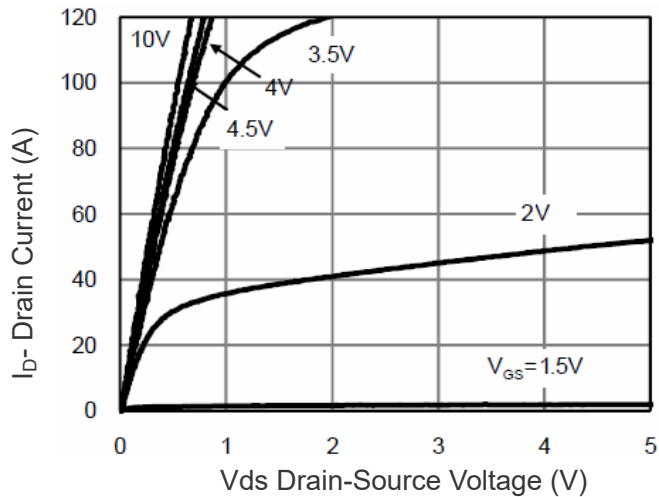


Figure 1 Output Characteristics

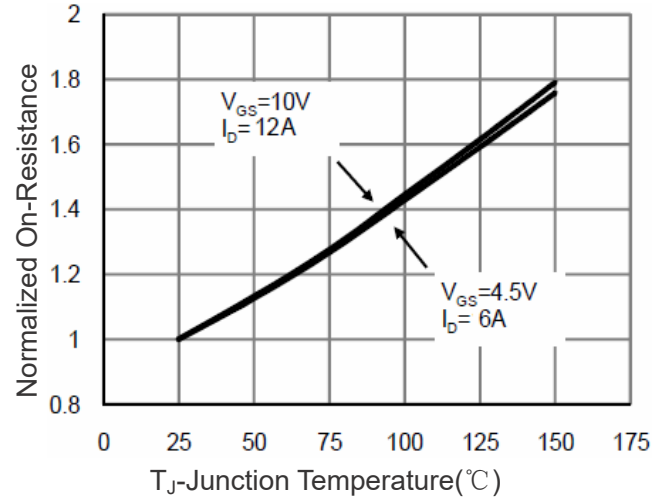


Figure 4 Rdson-Junction Temperature

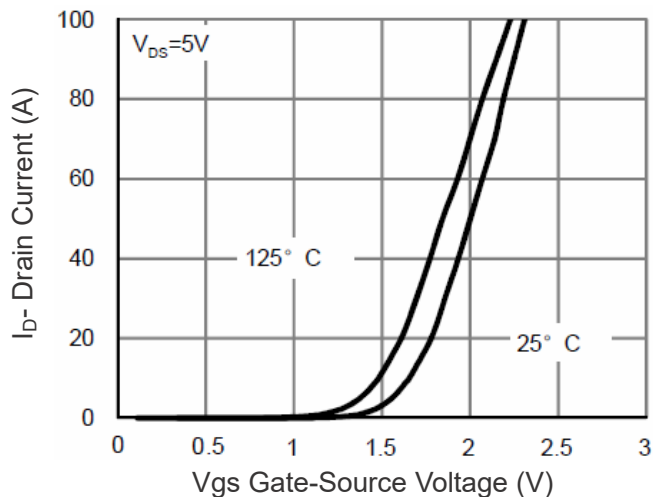


Figure 2 Transfer Characteristics

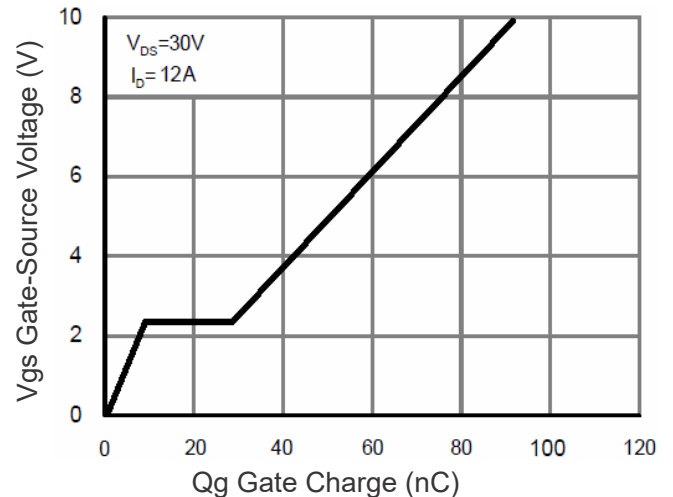


Figure 5 Gate Charge

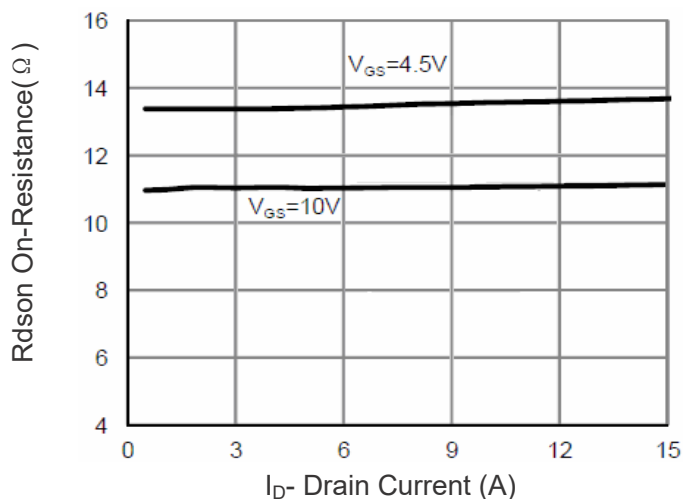


Figure 3 Rdson- Drain Current

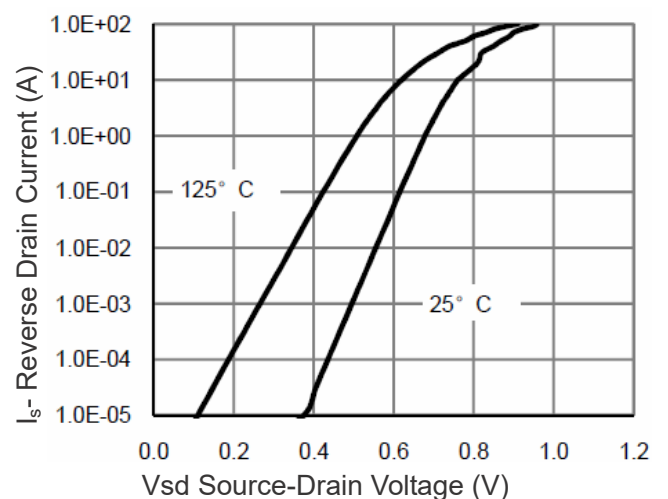


Figure 6 Source- Drain Diode Forward

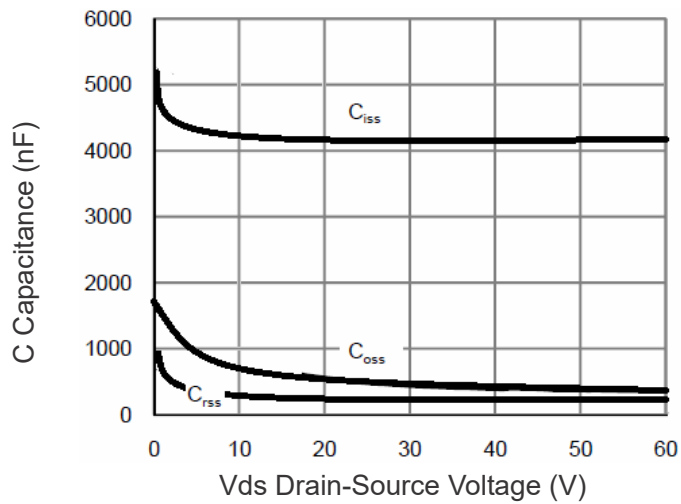


Figure 7 Capacitance vs Vds

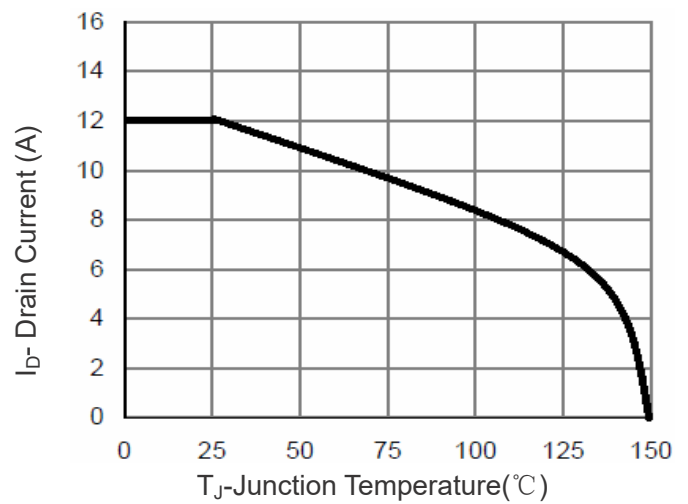


Figure 9 Current De-rating

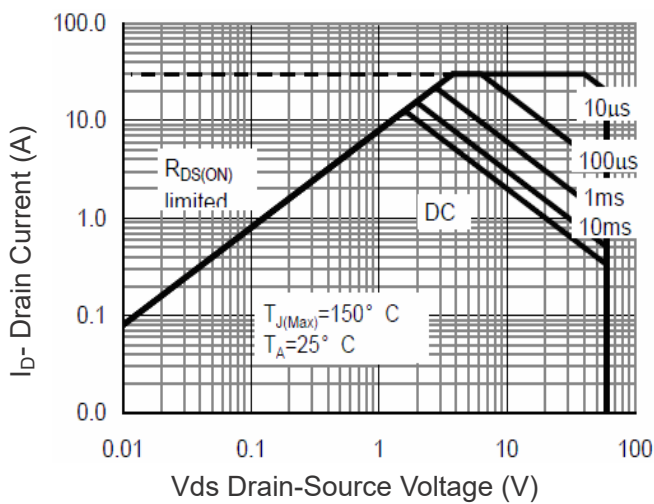


Figure 8 Safe Operation Area

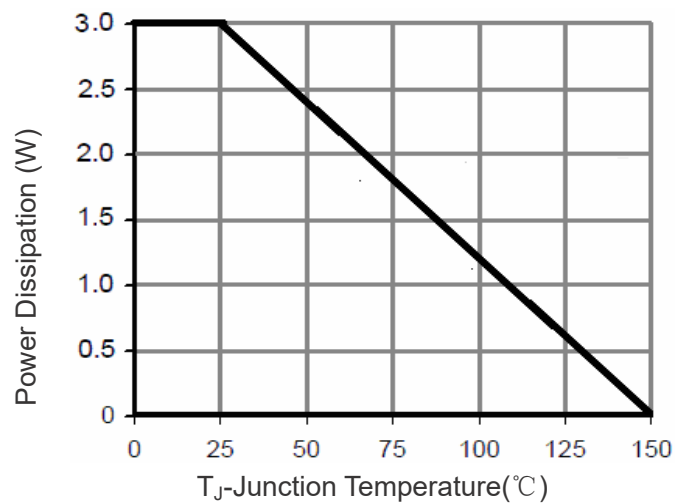


Figure 10 Power De-rating

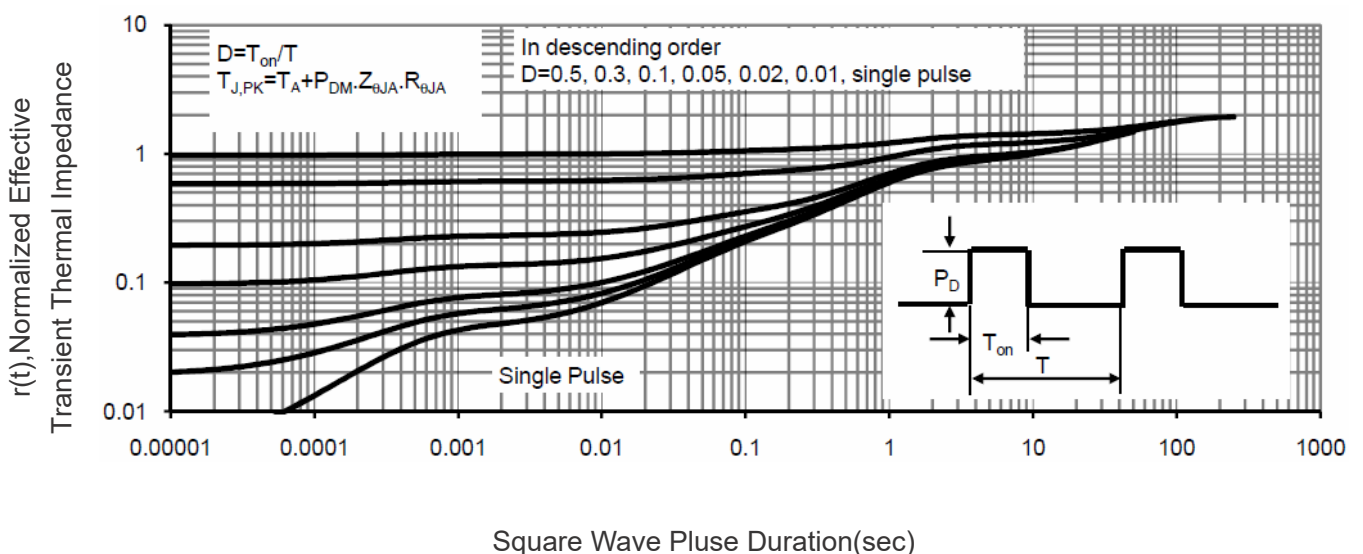
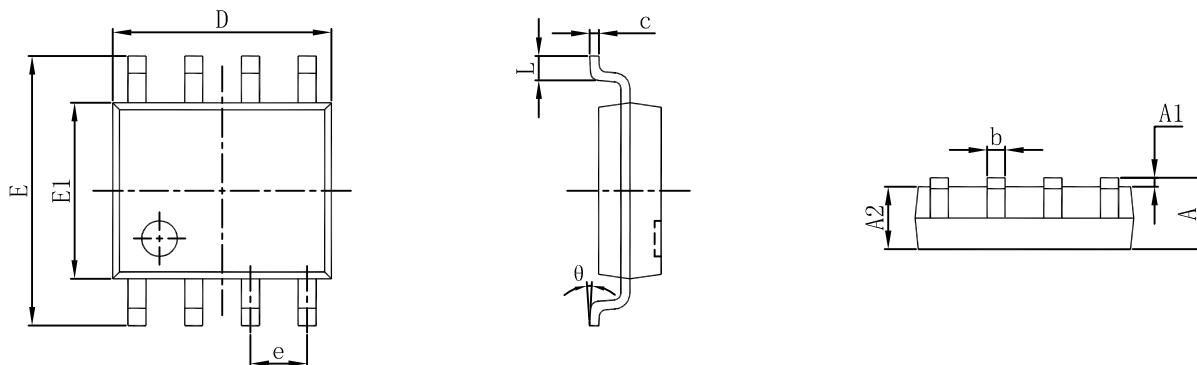


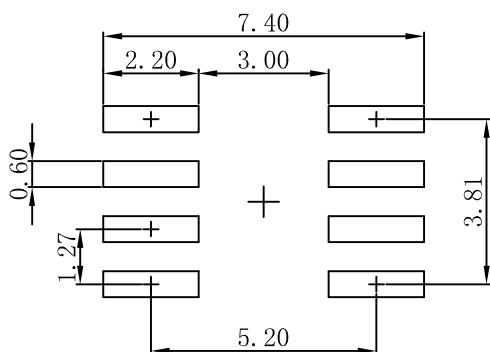
Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



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